Figure S1. Surface morphologies of the samples treated with RIE followed by HF/NH₄F etching. Left: 1- μ m RIE and 1- μ m HF/NH₄F etching, middle: 1- μ m RIE and 2- μ m HF/NH₄F etching, right: 1- μ m RIE and 3- μ m HF/NH₄F etching. The results showed that there was no obvious difference in surface morphology among the three HF/NH₄F-etched sample surfaces.



Figure S2. Raw data of the SC imaging for the six combined-etched samples. Left column: RIE and HF etching with removal amount of 1 μ m, 2 μ m, and 3 μ m. Right column: RIE and HF/NH₄F etching with removal amounts of 1 μ m, 2 μ m, and 3 μ m.

sample B1	sample C1
sample B2	sample C2
sample B3	sample C3
	사망이라는 그 것은 가지 않는. 전쟁에서 도망한 것은 전쟁이 전쟁에서 도망한 것은 전쟁이

Figure S3. Statistical data of the SC imaging for the six combined-etched samples. Left column: RIE and HF etching with removal amount of 1 μ m, 2 μ m, and 3 μ m. Right column: RIE and HF/NH₄F etching with removal amounts of 1 μ m, 2 μ m, and 3 μ m.



Figure S4. Raw data of the SC imaging for sample C3 (1-µm RIE and 3-µm HF/NH₄F etching).



Figure S5. Statistical data of the SC imaging for sample C3 (1- μ m RIE and 3- μ m HF/NH₄F etching).

